

ULTRA FAST RECOVERY RECTIFIER DIODES

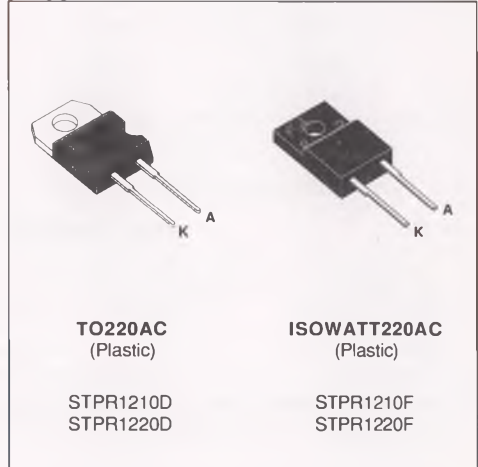
FEATURES

- SUITED FOR SMPS
- LOW LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY

DESCRIPTION

Low cost single chip rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in TO220AC and ISOWATT220AC, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit	
I_F (RMS)	RMS Forward Current		30	A	
I_F (AV)	Average Forward Current $\delta = 0.5$	TO220AC	$T_c = 115^\circ\text{C}$	12	A
		ISOWATT220AC	$T_c = 80^\circ\text{C}$		
I_{FSM}	Surge Non Repetitive Forward Current		$T_p = 10$ ms Sinusoidal	120	A
T_{stg} T_j	Storage and Junction Temperature Range		- 65 to + 150 - 65 to + 150		$^\circ\text{C}$

Symbol	Parameter	STPR		Unit
		1210D 1210F	1220D 1220F	
V_{RRM}	Repetitive Peak Reverse Voltage	100	200	V

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction-case	TO220AC	2.5	$^\circ\text{C/W}$
		ISOWATT220AC	5.0	

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _R RRM			50	μA
	T _j = 100°C				0.8	mA
V _F **	T _j = 125°C	I _F = 12 A			0.99	V
	T _j = 125°C	I _F = 24 A			1.20	
	T _j = 25°C	I _F = 24 A			1.25	

Pulse test : * t_p = 5 ms, duty cycle < 2 %
 ** t_p = 380 μs, duty cycle < 2%

RECOVERY CHARACTERISTICS

Symbol	Tests Conditions			Min.	Typ.	Max.	Unit
t _{rr}	T _j = 25°C	I _F = 0.5 A	I _R = 1A	I _{rr} = 0.25 A		30	ns
t _{fr}	T _j = 25°C	I _F = 1 A	t _r = 10 ns	V _{FR} = 1.1 x V _F	20		ns
V _{FP}	T _j = 25°C	I _F = 1 A	t _r = 10 ns		3		V

To evaluate the conduction losses use the following equation :
 $P = 0.78 \times I_F(\text{AV}) + 0.0175 I_F^2(\text{RMS})$

Fig.1 : Average forward power dissipation versus average forward current.

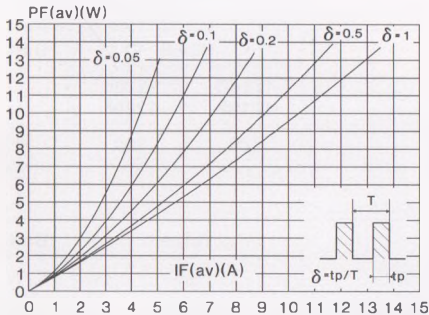


Fig.2 : Peak current versus form factor.

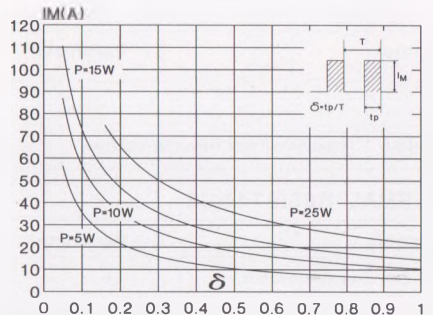


Fig.3 : Average current versus ambient temperature. (duty cycle : 0.5) (TO220AC)

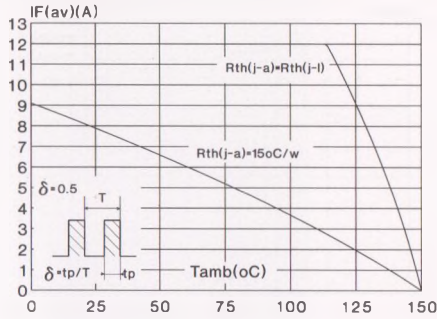


Fig.4 : Average current versus ambient temperature. (duty cycle : 0.5) (ISOWATT220AC)

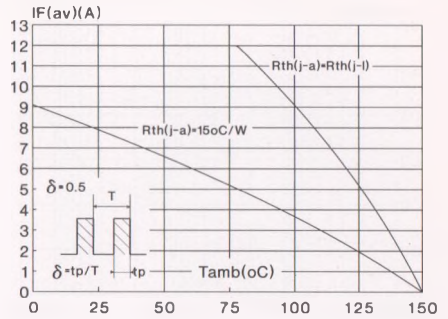


Fig.5 : Non repetitive surge peak forward current versus overload duration. (Maximum values) (TO220AC)

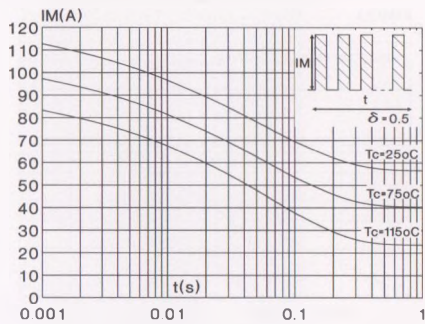


Fig.6 : Non repetitive surge peak forward current versus overload duration. (Maximum values) (ISOWATT220AC)

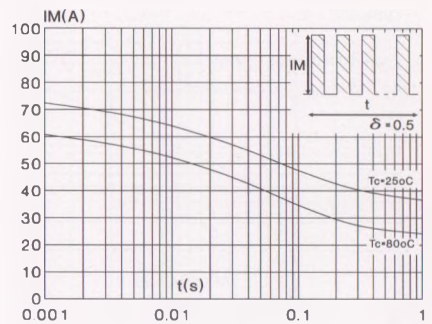


Fig.7 : Relative variation of thermal transient impedance junction to case versus pulse duration. (TO220AC)

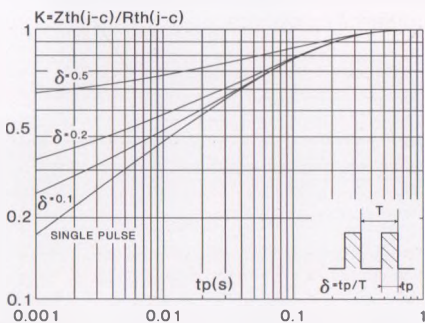


Fig.8 : Relative variation of thermal transient impedance junction to case versus pulse duration. (ISOWATT220AC)

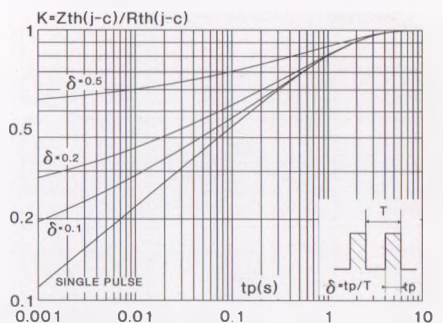


Fig.9 : Forward voltage drop versus forward current. (Maximum values)

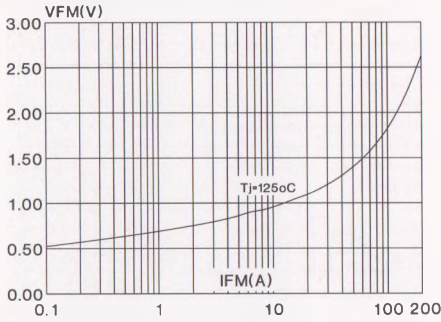


Fig.10 : Junction capacitance versus reverse voltage applied. (Typical values)

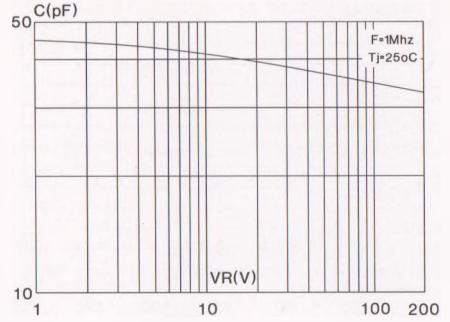


Fig.11 : Recovery charge versus dIF/dt.

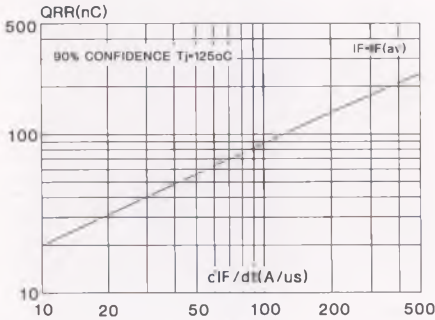


Fig.12 : Peak reverse current versus dIF/dt.

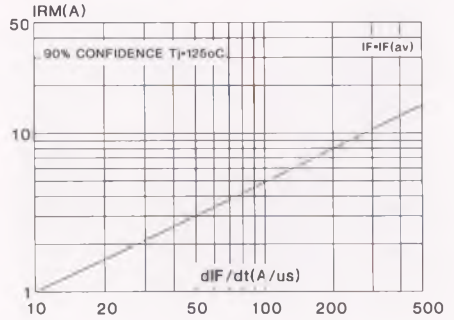


Fig.13 : Dynamic parameters versus junction temperature.

